

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOSV)

2SK2615

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 DC-DC CONVERTER, RELAY DRIVE AND MOTOR DRIVE
 APPLICATIONS

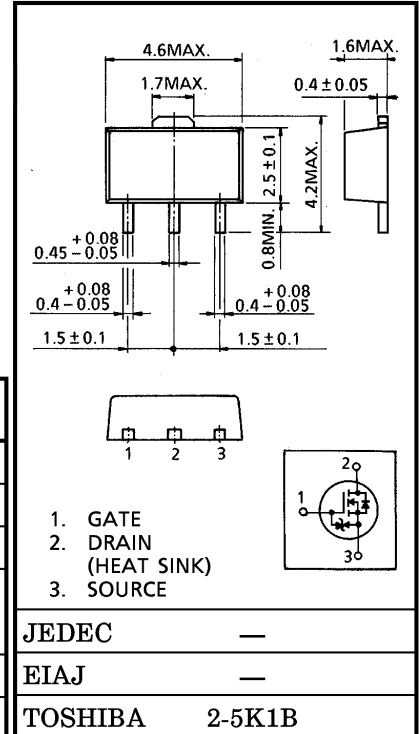
INDUSTRIAL APPLICATIONS

Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.23\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 2.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 60V$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	DC	I_D	2
	Pulse	I_{DP}	6
Drain Power Dissipation (Ta = 25°C)	P_D	0.5	W
Drain Power Dissipation	P_D^*	1.5	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 0.05g (Typ.)

MARKING



* : Mounted on ceramic substrate (600mm² × 0.8t)

THERMAL CHARACTERISTICS

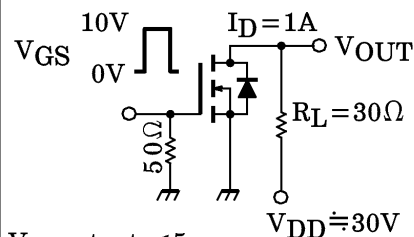
CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	250	°C/W

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±16V, VDS = 0V	—	—	±10	μA
Drain Cut-off Current		IDSS	VDS = 60V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V(BR)DSS	ID = 10mA, VGS = 0V	60	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	0.8	—	2.0	V
Drain-Source ON Resistance		RDS(ON)	VGS = 4V, ID = 1A	—	0.33	0.44	Ω
			VGS = 10V, ID = 1A	—	0.23	0.30	
Forward Transfer Admittance		Yfs	VDS = 10V, ID = 1A	1.0	2.0	—	S
Input Capacitance		Ciss	VDS = 10V, VGS = 0V, f = 1MHz	—	150	—	pF
Reverse Transfer Capacitance		Crss		—	25	—	
Output Capacitance		Coss		—	70	—	
Switching Time	Rise Time	tr	 <p>VIN : tr, tf < 5ns, Duty ≤ 1%, tw = 10μs</p>	—	25	—	ns
	Turn-on Time	ton		—	30	—	
	Fall Time	tf		—	50	—	
	Turn-off Time	toff		—	150	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 48V, VGS = 10V, ID = 2A	—	6.0	—	nC
Gate-Source Charge		Qgs		—	4.6	—	
Gate-Drain ("Miller") Charge		Qgd		—	1.4	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	2	A
Pulse Drain Reverse Current	IDRP	—	—	—	6	A
Diode Forward Voltage	VDSF	IDR = 2A, VGS = 0V	—	—	-1.5	V
Reverse Recovery Time	trr	IDR = 2A, VGS = 0V	—	100	—	ns
Reverse Recovered Charge	Qrr	dIDR / dt = 50A / μs	—	40	—	μC

